

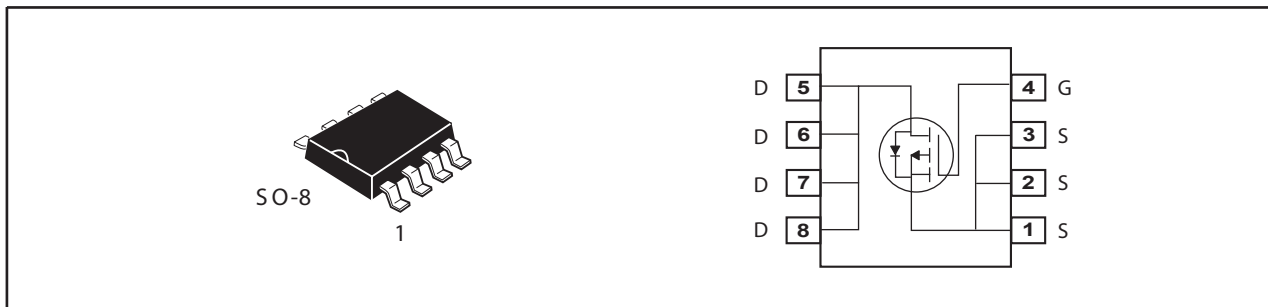


## P-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V <sub>DS</sub>	I <sub>D</sub>	R <sub>DS(ON)</sub> (mΩ) Max
-40V	-10A	14 @ V <sub>GS</sub> =-10V
		19 @ V <sub>GS</sub> =-4.5V

### FEATURES

- Super high dense cell design for low R<sub>DS(ON)</sub>.
- Rugged and reliable.
- Surface Mount Package.



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V <sub>DS</sub>	Drain-Source Voltage	-40	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-Continuous <sup>a e</sup>	T <sub>A</sub> =25°C	-10
		T <sub>A</sub> =70°C	-8
I <sub>DM</sub>	-Pulsed <sup>b</sup>	-56	A
E <sub>AS</sub>	Single Pulse Avalanche Energy <sup>d</sup>	56	mJ
P <sub>D</sub>	Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> =25°C	2.5
		T <sub>A</sub> =70°C	1.6
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C

### THERMAL CHARACTERISTICS

R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient <sup>a</sup>	50	°C/W
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# STM4417

Ver 1.0

## ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-40			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -32V , V <sub>GS</sub> =0V			-1	uA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V , V <sub>DS</sub> =0V			±100	nA
<b>ON CHARACTERISTICS</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1	-1.9	-3	V
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =-10V , I <sub>D</sub> =-5A		11	14	m ohm
		V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-4.3A		14	19	m ohm
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-10V , I <sub>D</sub> =-5A		22		S
<b>DYNAMIC CHARACTERISTICS <sup>c</sup></b>						
C <sub>ISS</sub>	Input Capacitance	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V f=1.0MHz		2900		pF
C <sub>OSS</sub>	Output Capacitance			345		pF
C <sub>RSS</sub>	Reverse Transfer Capacitance			285		pF
<b>SWITCHING CHARACTERISTICS <sup>c</sup></b>						
t <sub>D(ON)</sub>	Turn-On Delay Time	V <sub>DD</sub> =-20V I <sub>D</sub> =-1A V <sub>GS</sub> =-10V R <sub>GEN</sub> =6 ohm		43		ns
t <sub>r</sub>	Rise Time			59		ns
t <sub>D(OFF)</sub>	Turn-Off Delay Time			177		ns
t <sub>f</sub>	Fall Time			66		ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-20V, I <sub>D</sub> =-5A, V <sub>GS</sub> =-10V		62		nC
		V <sub>DS</sub> =-20V, I <sub>D</sub> =-5A, V <sub>GS</sub> =-4.5V		30		nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =-20V, I <sub>D</sub> =-5A,		6		nC
Q <sub>gd</sub>	Gate-Drain Charge	V <sub>GS</sub> =-10V		16.5		nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A		-0.78	-1.2	V
<b>Notes</b>						
a.Surface Mounted on FR4 Board, t ≤ 10sec.						
b.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.						
c.Guaranteed by design, not subject to production testing.						
d.Starting T <sub>J</sub> =25°C, L=0.5mH, V <sub>DD</sub> = 20V.(See Figure13)						
e.Drain current limited by maximum junction temperature.						

Apr,24,2013

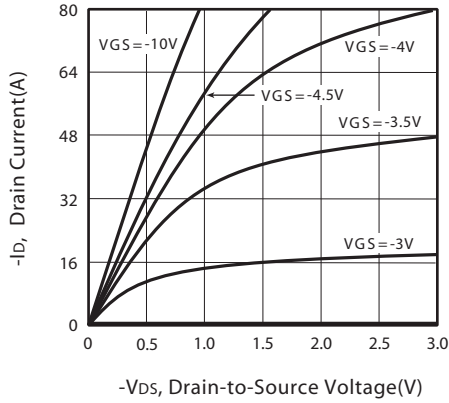


Figure 1. Output Characteristics

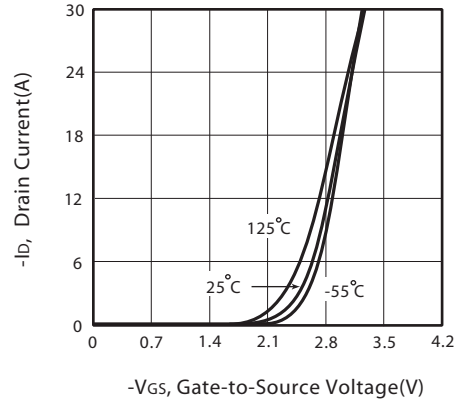


Figure 2. Transfer Characteristics

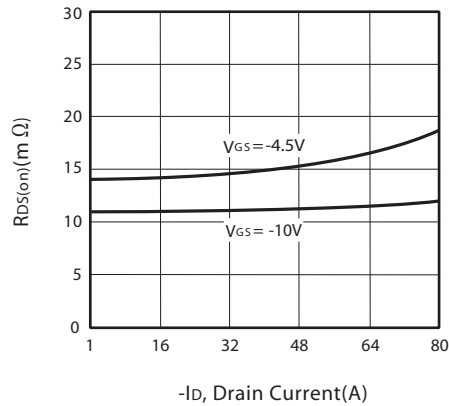


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

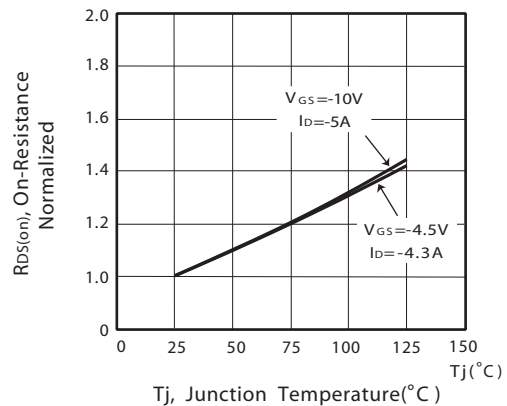


Figure 4. On-Resistance Variation with Drain Current and Temperature

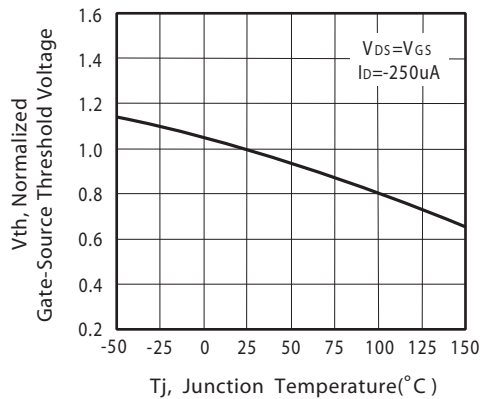


Figure 5. Gate Threshold Variation with Temperature

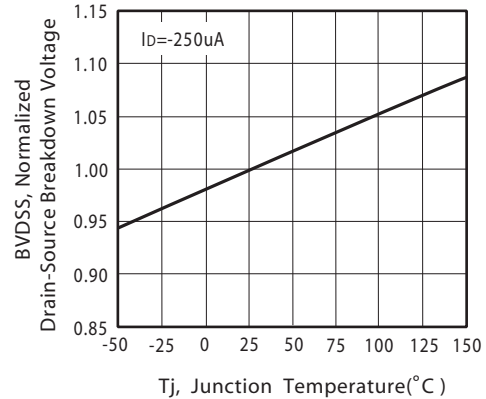


Figure 6. Breakdown Voltage Variation with Temperature

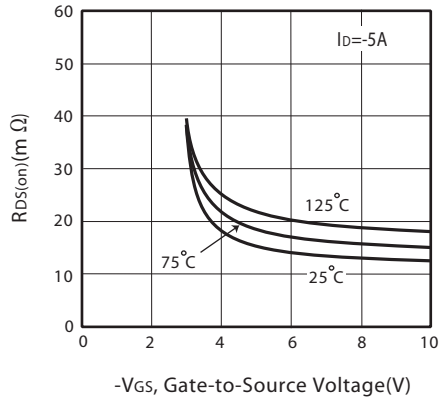


Figure 7. On-Resistance vs. Gate-Source Voltage

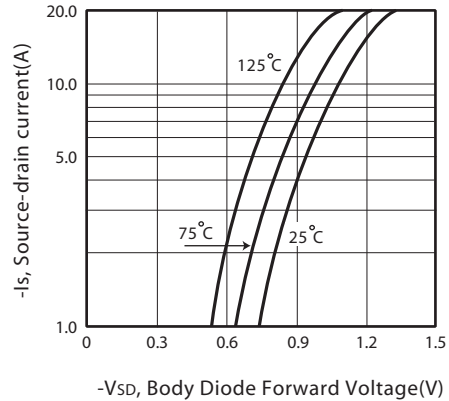


Figure 8. Body Diode Forward Voltage Variation with Source Current

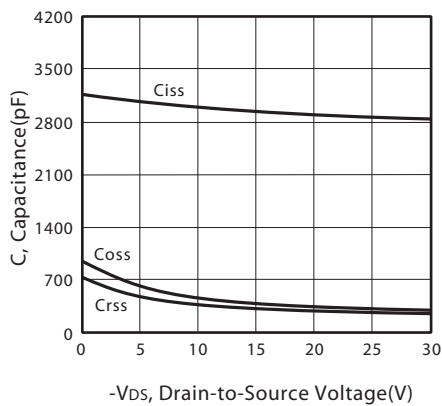


Figure 9. Capacitance

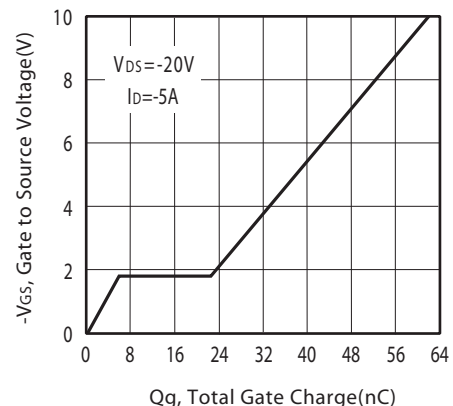


Figure 10. Gate Charge

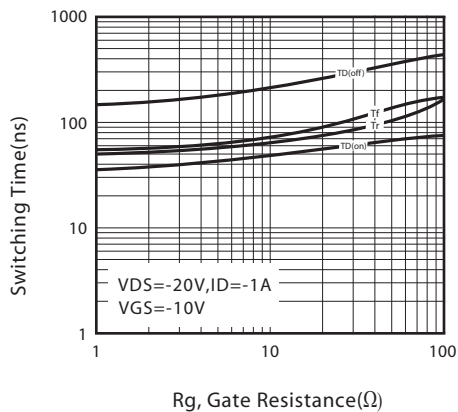


Figure 11. switching characteristics

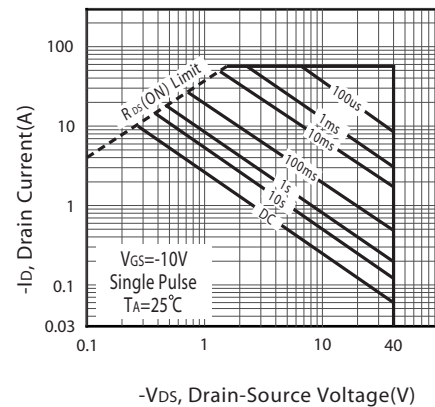
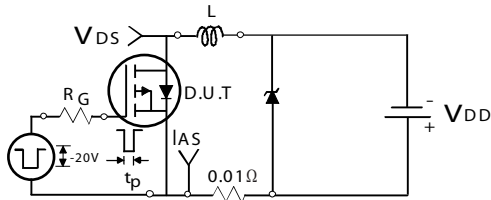
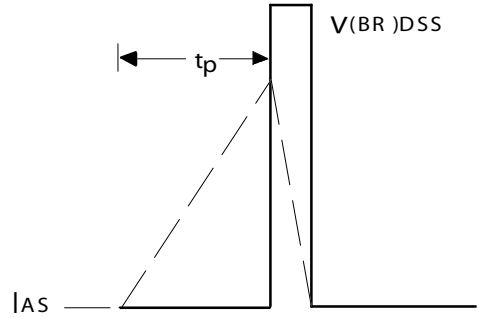


Figure 12. Maximum Safe Operating Area



Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

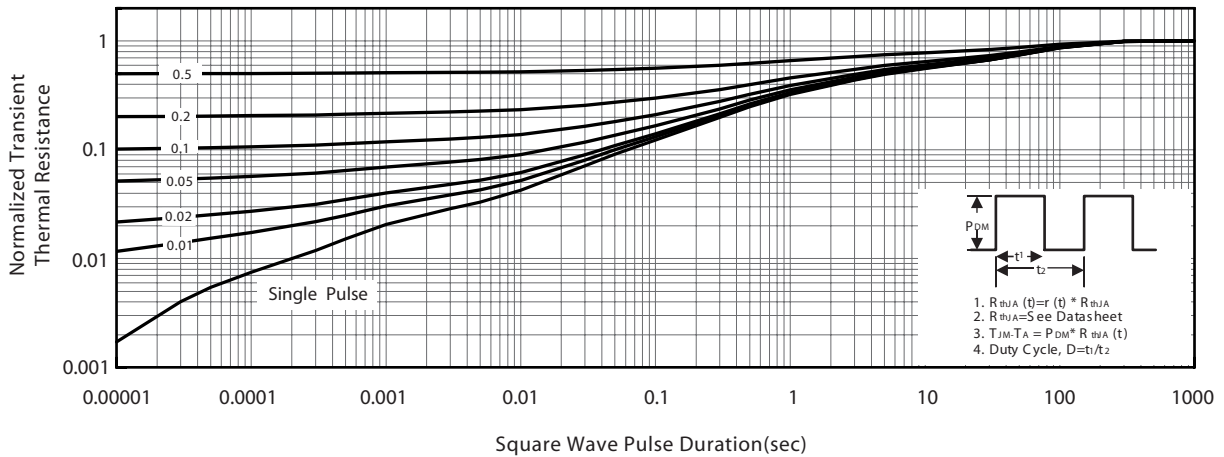
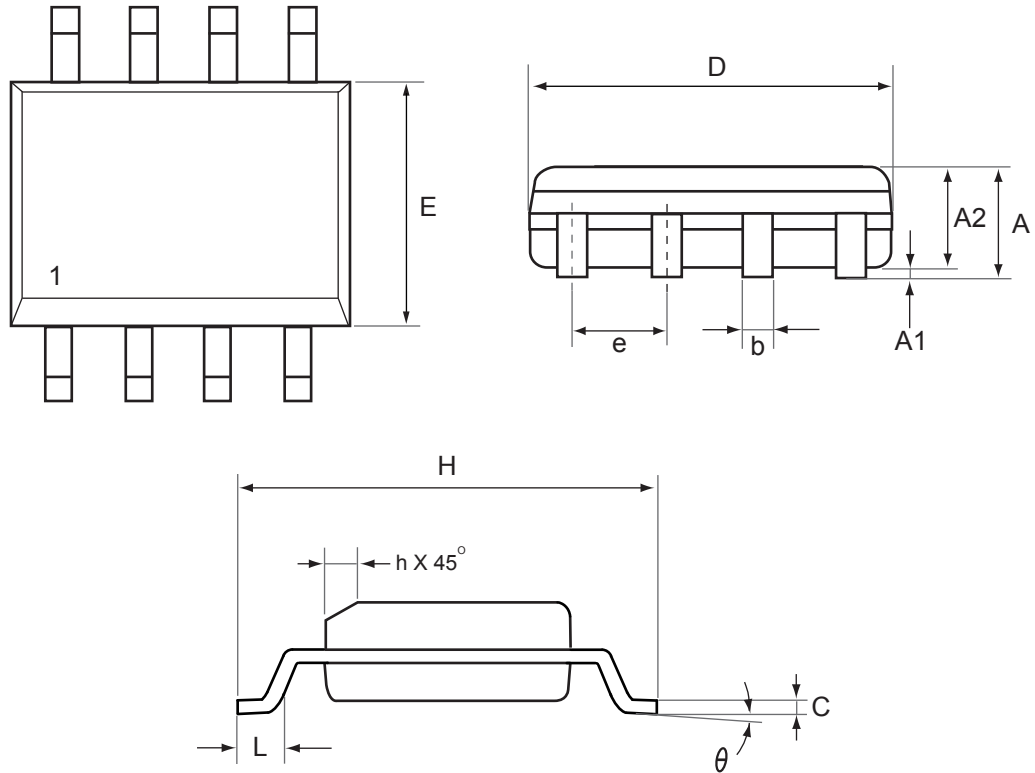


Figure 14. Normalized Thermal Transient Impedance Curve

## PACKAGE OUTLINE DIMENSIONS

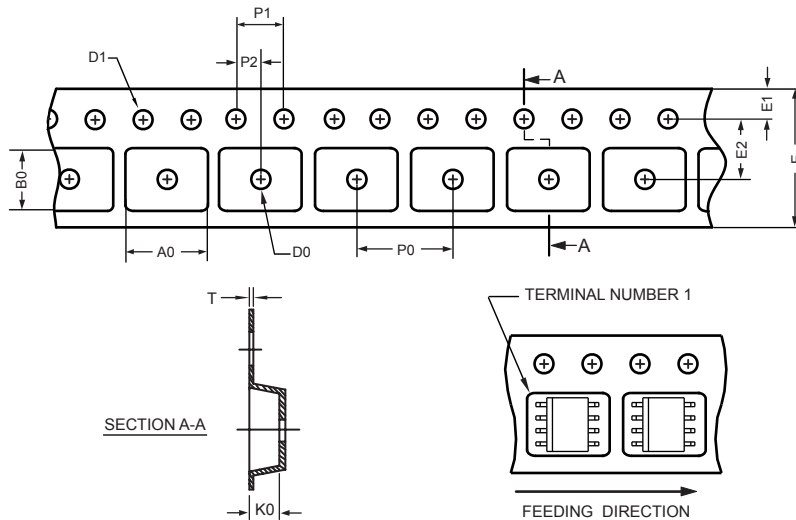
SO-8



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
A2	1.25	1.63	0.049	0.064
b	0.31	0.51	0.012	0.020
C	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	3.70	4.00	0.146	0.157
e	1.27 REF.		0.050 BSC	
H	5.80	6.20	0.228	0.244
L	0.40	1.27	0.016	0.050
θ	0°	8°	0°	8°
h	0.25	0.50	0.010	0.020

## SO-8 Tape and Reel Data

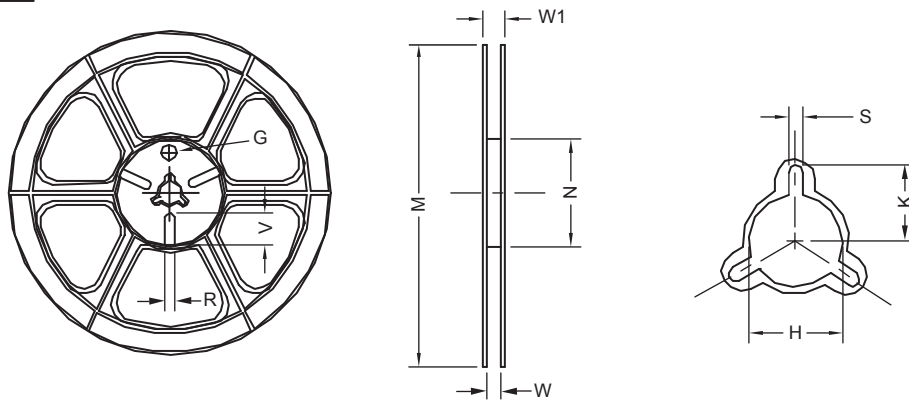
### SO-8 Carrier Tape



unit:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOP 8N 150mil	6.50 ±0.15	5.25 ±0.10	2.10 ±0.10	φ 1.5 (MIN)	φ 1.55 ±0.10	12.0 +0.3 - 0.1	1.75 ±0.10	5.5 ±0.10	8.0 ±0.10	4.0 ±0.10	2.0 ±0.10	0.30 ±0.013

### SO-8 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	φ 330	330 ± 1	62 ±1.5	12.4 + 0.2	16.8 - 0.4	φ 12.75 + 0.15	---	2.0 ±0.15	---	---	---